MOTOROLA2供应商 SEMICONDUCTOR TECHNICAL DATA

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Designer's™ Data Sheet Complementary NPN-PNP Silicon Power Bipolar Transistor

- The MJL3281A and MJL1302A are PowerBase power transistors for high power audio, disk head positioners and other linear applications.
- Designed for 100 W Audio Frequency
- Gain Complementary:
 - Gain Linearity from 100 mA to 7 A
 - High Gain 60 to 175
 - h_{FE} = 45 (Min) @ I_C = 8 A
- Low Harmonic Distortion
- High Safe Operation Area 1 A/100 V @ 1 sec
- High fT 30 MHz Typical



*Motorola Preferred Device

15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 200 VOLTS 200 WATTS



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	VCEO	200	Vdc	
Collector-Base Voltage	VCBO	200	Vdc	
Emitter-Base Voltage	V _{EBO}	V _{EBO} 7		
Collector-Emitter Voltage - 1.5 V	VCEX	200	Vdc	
Collector Current — Continuous — Peak ⁽¹⁾	IC	15 25	Adc	
Base Current — Continuous	Ι _Β	1.5	Adc	
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	PD	200 1.43	Watts W/°C	
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-65 to +150	°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	0.7	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle <10%.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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referred devices are Motorola recommended choices for future use and best overall value.

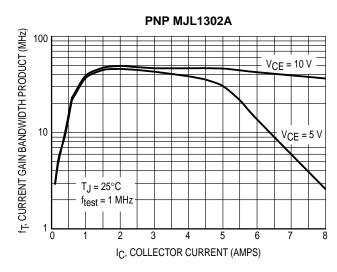


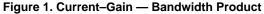
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	200	-	_	Vdc
Emitter–Base Voltage ($I_E = 100 \ \mu Adc, I_C = 0$)	VEBO	7	-	—	Vdc
Collector Cutoff Current ($V_{CB} = 200 \text{ Vdc}, I_E = 0$)	ІСВО	_	-	50	μAdc
Emitter Cutoff Current (V _{EB} = 5 Vdc, I _C = 0)	IEBO	_	-	5	μAdc
Emitter Cutoff Current ($V_{EB} = 7 Vdc, I_C = 0$)	IEBO	—	-	25	μAdc
SECOND BREAKDOWN			•	•	
Second Breakdown Collector with Base Forward Biased ($V_{CE} = 50 \text{ Vdc}$, t = 1 s (non-repetitive) ($V_{CE} = 100 \text{ Vdc}$, t = 1 s (non-repetitive)	I _{S/b}	4 1			Adc
ON CHARACTERISTICS			•	•	
DC Current Gain (I _C = 100 mAdc, V _{CE} = 5 Vdc) (I _C = 1 Adc, V _{CE} = 5 Vdc) (I _C = 3 Adc, V _{CE} = 5 Vdc) (I _C = 5 Adc, V _{CE} = 5 Vdc) (I _C = 7 Adc, V _{CE} = 5 Vdc) (I _C = 8 Adc, V _{CE} = 5 Vdc) (I _C = 15 Adc, V _{CE} = 5 Vdc)	hFE	60 60 60 60 45 12	125 — — 115 — 35	175 175 175 175 175 175 	
Collector–Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 1 \text{ Adc})$	VCE(sat)	_	-	3	Vdc
DYNAMIC CHARACTERISTICS			•	•	•
Current–Gain — Bandwidth Product (I _C = 1 Adc, V _{CE} = 5 Vdc, f _{test} = 1 MHz)	fT	_	30	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	_	-	600	pF

(1) Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS





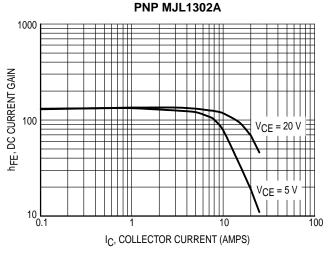


Figure 3. DC Current Gain

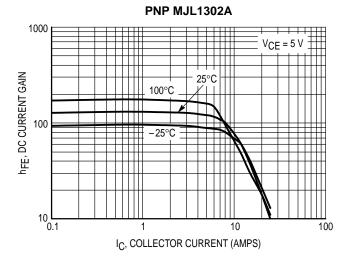


Figure 5. DC Current Gain, V_{CE} = 5 V

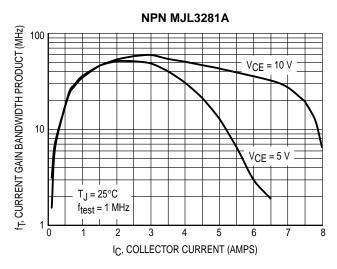


Figure 2. Current–Gain — Bandwidth Product

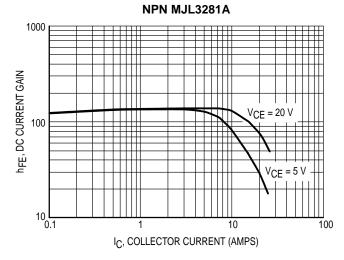
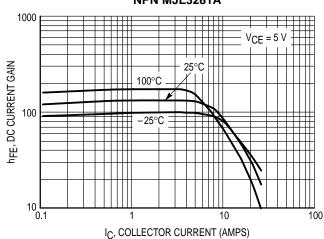


Figure 4. DC Current Gain



NPN MJL3281A

Figure 6. DC Current Gain, V_{CE} = 5 V

TYPICAL CHARACTERISTICS

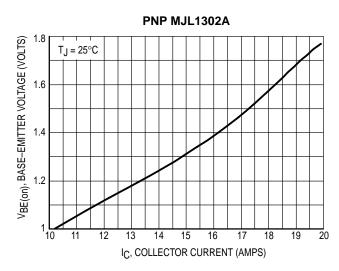


Figure 7. Typical Base–Emitter Voltage

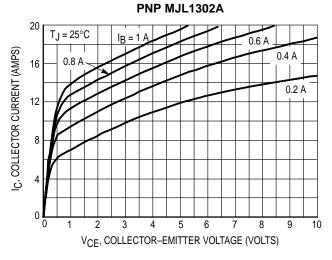


Figure 9. Typical Output Characteristics

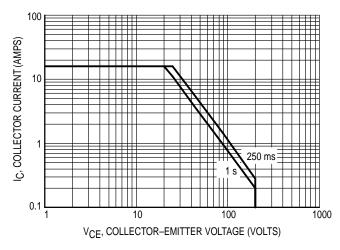


Figure 11. Forward Bias Safe Operating Area (FBSOA)

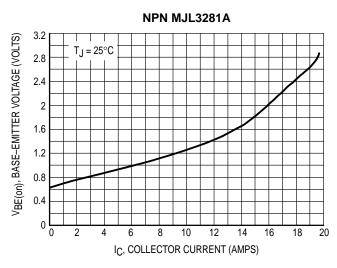


Figure 8. Typical Base–Emitter Voltage

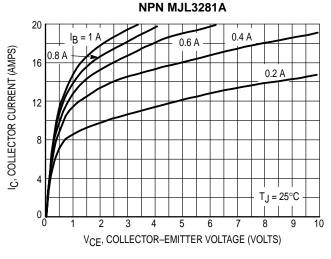
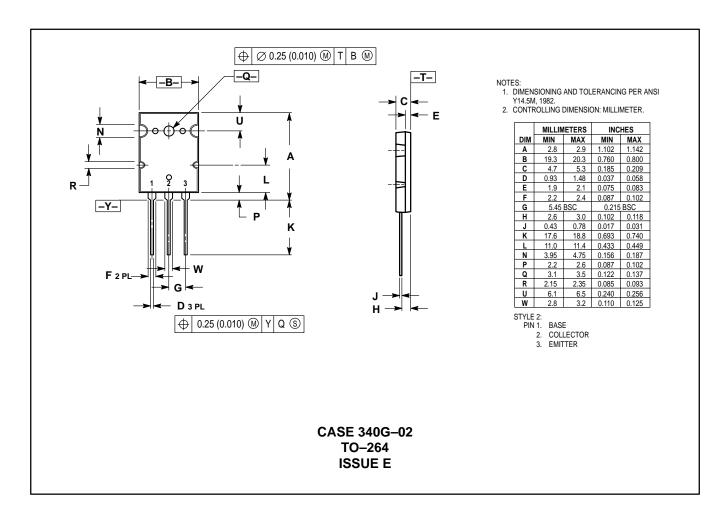


Figure 10. Typical Output Characteristics

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.





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